

01. →



FIG. 1

200 - Formation of barrier layer  
(optional)

210 - Formation of dielectric layer

220 - Pattern + etch of <sup>the</sup> dielectric layer and ~~remove~~ the barrier layer (if used)

230 - Barrier metal and Copper deposition

240 - Copper CMP

260 - Post-CMP clean

280 - Formation of next dielectric layer

FIG. 2

TI-35330  
RAK

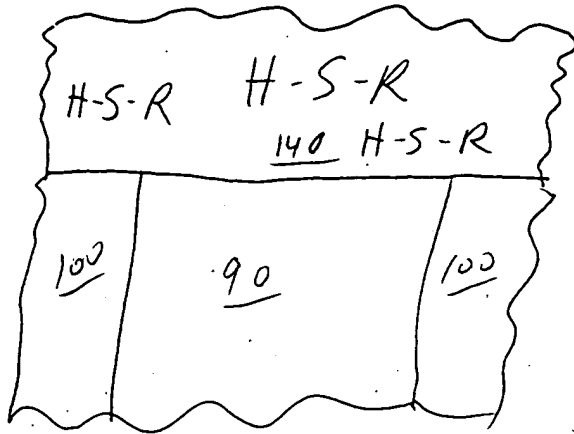


FIG. 3A

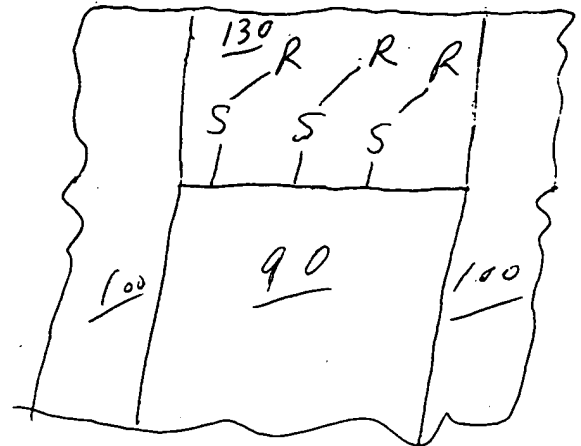


FIG. 3B

TI-35330  
RHK

